

# isc N-Channel MOSFET Transistor

# SPP12N50C3, ISPP12N50C3

#### • FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on) ≤0.38Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

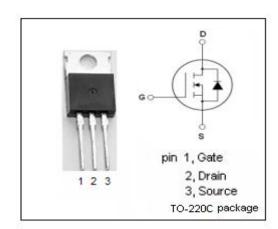
- · New revolutionary high voltage technology
- Ultra low effective capacitance

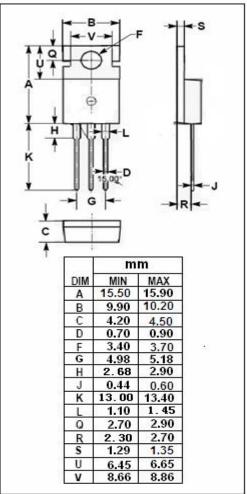
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                               | VALUE   | UNIT       |  |
|------------------|---|---------|------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                    | 500     | V          |  |
| V <sub>GS</sub>  | Gate-Source Voltage                     | ±20     | V          |  |
| I <sub>D</sub>   | Drain Current-Continuous 11.            |         | А          |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed             | 34.8    | А          |  |
| P <sub>D</sub>   | Total Dissipation @T <sub>c</sub> =25℃  | 125     | W          |  |
| Tj               | Max. Operating Junction Temperature 150 |         | $^{\circ}$ |  |
| T <sub>stg</sub> | Storage Temperature                     | -55~150 | $^{\circ}$ |  |

### THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                                       | MAX | UNIT |  |  |  |  |
|-----------|---|-----|------|--|--|--|--|
| Rth(ch-c) | Channel-to-case thermal resistance              | 1   | °C/W |  |  |  |  |
| Rth(ch-a) | Rth(ch-a) Channel-to-ambient thermal resistance |     | °C/W |  |  |  |  |







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | ТҮР | MAX  | UNIT |
|---------------------|--------------------------------|--|-----|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A               | 500 |     |      | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =500 μ A | 2.1 |     | 3.9  | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =7A                   |     |     | 0.38 | Ω    |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> =20V; V <sub>DS</sub> =0V                  |     |     | 0.1  | μА   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =500V; V <sub>GS</sub> = 0V                |     |     | 1    | μА   |
| V <sub>SD</sub>     | Diode forward voltage          | IF=Is; V <sub>GS</sub> = 0V                                |     |     | 1.2  | V    |

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